N-Channel General-Purpose Amplifier

MMBFJ201, MMBFJ202

Description

This device is designed primarily for low level audio and general-purpose applications with high impedance signal sources. Sourced from process 52.

Applications

• These are Pb-Free Devices

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted) (Note 1, 2)

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	40	V
V _{GS}	Gate-Source Voltage	-40	V
I _{GF}	Forward Gate Current	50	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150 $^{\circ}\text{C}.$
- These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

THERMAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Note 3)

Symbol	Parameter	Max	Unit
P _D	Total Device Dissipation	350	mW
	Derate Above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

 Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6 cm².



ON Semiconductor®

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SOT-23 (TO-236) CASE 318-08



SOT-23 CASE 318BM

MARKING DIAGRAMS



62x = Specific Device Code

x = P or Q M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Downloaded from Arrow.com.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	on	Min	Max	Unit
OFF CHARA	ACTERISTICS					
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_G = -1.0 \mu\text{A}, V_{DS} = 0$		-40	-	V
I _{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$		-	-100	pА
V _{GS} (off)	Gate-Source Cut-Off Voltage	V _{DS} = 20 V, I _D = 10 nA	MMBFJ201	-0.3	-1.5	V
			MMBFJ202	-0.8	-4.0	1
ON CHARA	CTERISTICS					•
I _{DSS}	Zero-Gate Voltage Drain Current (Note 4)	V _{DS} = 20 V, I _{GS} = 0	MMBFJ201	0.2	1.0	mA
			MMBFJ202	0.9	4.5	1
SMALL SIG	NAL CHARACTERISTICS					
УFS	Forward Transfer Admittance	V _{DS} = 20 V, f = 1.0 kHz	MMBFJ201	500		μmhos
			MMBFJ202	1000		1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse test: pulse width \leq 300 μ s, duty cycle \leq 2%.

TYPICAL PERFORMANCE CHARACTERISTICS

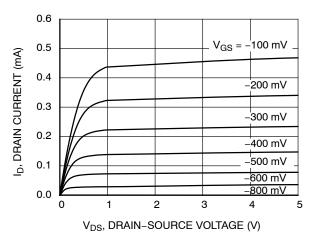


Figure 1. Common Drain-Source (MMBJF201)

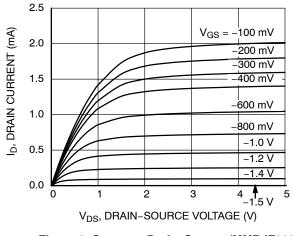


Figure 2. Common Drain-Source (MMBJF202)

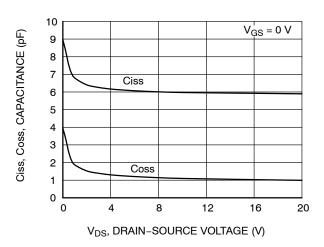


Figure 3. Capacitance vs. Voltage (MMBJF201)

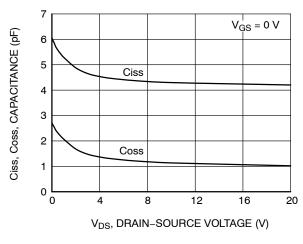


Figure 4. Capacitance vs. Voltage (MMBJF202)

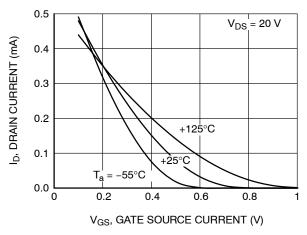


Figure 5. Transfer Characteristics (MMBFJ201)

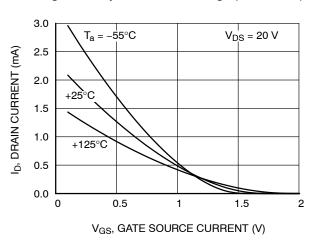


Figure 6. Transfer Characteristics (MMBFJ202)

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

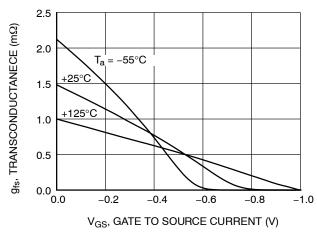
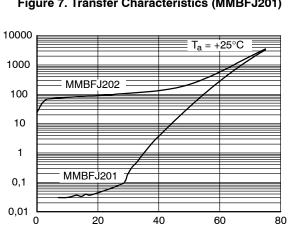


Figure 7. Transfer Characteristics (MMBFJ201)



V_{DG} (V) Figure 9. Leakage Current vs. Voltage

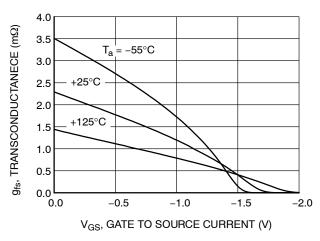


Figure 8. Transfer Characteristics (MMBFJ202)

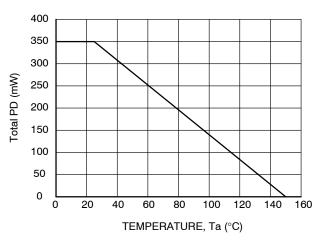


Figure 10. Total PD vs. Temperature

I_{GSS}, GATE LEAKAGE CURRENT (nA)

ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]
MMBFJ201	62P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBFJ202	62Q	SOT-23 (TO-236) (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

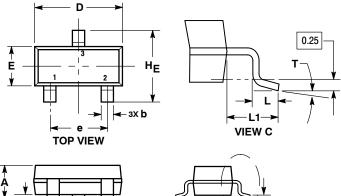


SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

10°

SCALE 4:1



SEE VIEW C

END VIEW

NOTES:

0°

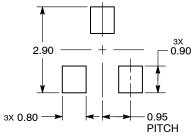
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	М	ILLIMETE	RS	INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Не	2.10	2.40	2.64	0.002	0.004	0.104

10°

RECOMMENDED SOLDERING FOOTPRINT

SIDE VIEW

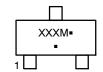


DIMENSIONS: MILLIMETERS

STYLE 28: PIN 1. ANODE 2. ANODE

3. ANODE

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1

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STYLE 27: PIN 1. CATHODE 2. CATHODE

3. CATHODE



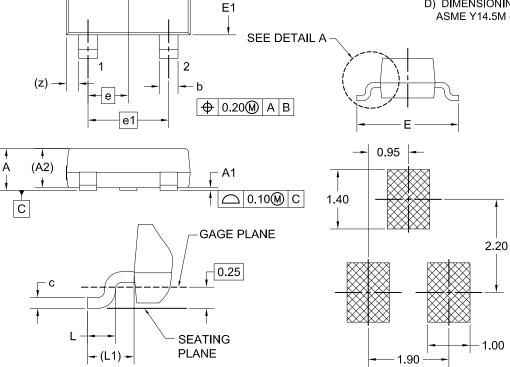


SOT-23 CASE 318BM ISSUE A

DATE 01 SEP 2021

NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 2009.



Α

В

2000.			
DIM	N	IILLIMET	ERS
Diw	MIN.	NOM.	MAX.
Α			1.20
A1	0.00	0.05	0.10
A2	0).93 REF	
b	0.37	0.44	0.60
С	0.08	0.15	0.23
D	2.72	2.92	3.12
Е	2.10	2.40	2.70
E1	1.15	1.30	1.50
е	(0.95 BSC	;
e1	,	1.90 BSC	;
L	0.20		
L1	().55 REF	
z	().29 REF	

GENERIC MARKING DIAGRAM*

DETAIL A



PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

LAND PATTERN
RECOMMENDATION
*FOR ADDITIONAL INFORMATION ON OUR

XXX = Specific Device Code
M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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